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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	HCS12X
Core Size	16-Bit
Speed	50MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SCI, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	59
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.72V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	80-QFP
Supplier Device Package	80-QFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s12xeq512maa

1.2.3.7 PA[7:0] / ADDR[15:8] / IVD[15:8] — Port A I/O Pins

PA[7:0] are general-purpose input or output pins. In MCU expanded modes of operation, these pins are used for the external address bus. In MCU emulation modes of operation, these pins are used for external address bus and internal visibility read data.

1.2.3.8 PB[7:1] / ADDR[7:1] / IVD[7:1] — Port B I/O Pins

PB[7:1] are general-purpose input or output pins. In MCU expanded modes of operation, these pins are used for the external address bus. In MCU emulation modes of operation, these pins are used for external address bus and internal visibility read data.

1.2.3.9 PB0 / ADDR0 / $\overline{\text{UDS}}$ / IVD[0] — Port B I/O Pin 0

PB0 is a general-purpose input or output pin. In MCU expanded modes of operation, this pin is used for the external address bus ADDR0 or as upper data strobe signal. In MCU emulation modes of operation, this pin is used for external address bus ADDR0 and internal visibility read data IVD0.

1.2.3.10 PC[7:0] / DATA [15:8] — Port C I/O Pins

PC[7:0] are general-purpose input or output pins. In MCU expanded modes of operation, these pins are used for the external data bus.

The input voltage thresholds for PC[7:0] can be configured to reduced levels, to allow data from an external 3.3-V peripheral to be read by the MCU operating at 5.0 V. The input voltage thresholds for PC[7:0] are configured to reduced levels out of reset in expanded and emulation modes. The input voltage thresholds for PC[7:0] are configured to 5-V levels out of reset in normal modes.

1.2.3.11 PD[7:0] / DATA [7:0] — Port D I/O Pins

PD[7:0] are general-purpose input or output pins. In MCU expanded modes of operation, these pins are used for the external data bus.

The input voltage thresholds for PD[7:0] can be configured to reduced levels, to allow data from an external 3.3-V peripheral to be read by the MCU operating at 5.0 V. The input voltage thresholds for PD[7:0] are configured to reduced levels out of reset in expanded and emulation modes. The input voltage thresholds for PC[7:0] are configured to 5-V levels out of reset in normal modes.

1.2.3.12 PE7 / ECLKX2 / $\overline{\text{XCLKS}}$ — Port E I/O Pin 7

PE7 is a general-purpose input or output pin. ECLKX2 is a free running clock of twice the internal bus frequency, available by default in emulation modes and when enabled in other modes. The $\overline{\text{XCLKS}}$ is an input signal which controls whether a crystal in combination with the internal loop controlled Pierce oscillator is used or whether full swing Pierce oscillator/external clock circuitry is used (refer to Oscillator Configuration). An internal pullup is enabled during reset.

Table 2-33. PTM Register Field Descriptions (continued)

Field	Description
4 PTM	**Port M general purpose input/output data**—Data Register Port M pin 4 is associated with the RXCAN signal of CAN2 and the routed CAN4 and CAN0, as well as with MOSI signals of SPI0. The CAN2 function takes precedence over the routed CAN0, routed CAN4, the routed SPI0 and the general purpose I/O function if the CAN2 module is enabled. The routed CAN0 function takes precedence over the routed CAN4, the routed SPI0 and the general purpose I/O function if the routed CAN0 module is enabled. The routed CAN4 function takes precedence over the routed SPI0 and general purpose I/O function if the routed CAN4 module is enabled. The routed SPI0 function takes precedence of the general purpose I/O function if the routed SPI0 is enabled. When not used with the alternative function, this pin can be used as general purpose I/O. If the associated data direction bit of this pin is set to 1, a read returns the value of the port register, otherwise the buffered pin input state is read.
3 PTM	**Port M general purpose input/output data**—Data Register Port M pin 5 is associated with the TXCAN signal of CAN1 and the routed CAN0, as well as with $\overline{SS0}$ signals of SPI0. The CAN1 function takes precedence over the routed CAN0, the routed SPI0 and the general purpose I/O function if the CAN1 module is enabled. The routed CAN0 function takes precedence over the routed SPI0 and the general purpose I/O function if the routed CAN0 module is enabled. The routed SPI0 function takes precedence of the general purpose I/O function if the routed SPI0 is enabled. When not used with the alternative function, this pin can be used as general purpose I/O. If the associated data direction bit of this pin is set to 1, a read returns the value of the port register, otherwise the buffered pin input state is read.
2 PTM	**Port M general purpose input/output data**—Data Register Port M pin 4 is associated with the RXCAN signal of CAN1 and the routed CAN0, as well as with MISO signals of SPI0. The CAN1 function takes precedence over the routed CAN0, the routed SPI0 and the general purpose I/O function if the CAN1 module is enabled. The routed CAN0 function takes precedence over the routed SPI0 and the general purpose I/O function if the routed CAN0 module is enabled. The routed SPI0 function takes precedence of the general purpose I/O function if the routed SPI0 is enabled. When not used with the alternative function, this pin can be used as general purpose I/O. If the associated data direction bit of this pin is set to 1, a read returns the value of the port register, otherwise the buffered pin input state is read.
1-0 PTM	**Port M general purpose input/output data**—Data Register Port M pins 1 and 0 are associated with TXCAN and RXCAN signals of CAN0, respectively. When not used with the alternative function, this pin can be used as general purpose I/O. If the associated data direction bit of this pin is set to 1, a read returns the value of the port register, otherwise the buffered pin input state is read.

2.3.38 Port M Input Register (PTIM)

Address 0x0251 Access: User read(1)

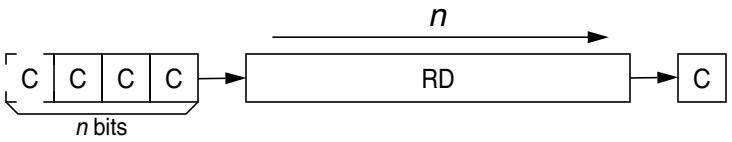
	7	6	5	4	3	2	1	0
R	PTIM7	PTIM6	PTIM5	PTIM4	PTIM3	PTIM2	PTIM1	PTIM0
W								
Reset	u	u	u	u	u	u	u	u

= Unimplemented or Reserved u = Unaffected by reset

Figure 2-36. Port M Input Register (PTIM)

CSR Logical Shift Right with Carry CSR

Operation



n = RS or IMM4

Shifts the bits in register RD *n* positions to the right. The higher *n* bits of the register RD become filled with the carry flag. The carry flag will be updated to the bit contained in RD[n-1] before the shift for *n* > 0. *n* can range from 0 to 16.

In immediate address mode, *n* is determined by the operand IMM4. *n* is considered to be 16 if IMM4 is equal to 0.

In dyadic address mode, *n* is determined by the content of RS. *n* is considered to be 16 if the content of RS is greater than 15.

CCR Effects

N	Z	V	C
Δ	Δ	Δ	Δ

N: Set if bit 15 of the result is set; cleared otherwise.

Z: Set if the result is $0000; cleared otherwise.

V: Set if a two´s complement overflow resulted from the operation; cleared otherwise.
$RD[15]_{old}$ ^ $RD[15]_{new}$

C: Set if *n* > 0 and RD[n-1] = 1; if n = 0 unaffected.

Code and CPU Cycles

Source Form	Address Mode	Machine Code												Cycles
CSR RD, #IMM4	IMM4	0	0	0	0	1	RD	IMM4		1	0	1	1	P
CSR RD, RS	DYA	0	0	0	0	1	RD	RS	1	0	0	1	1	P

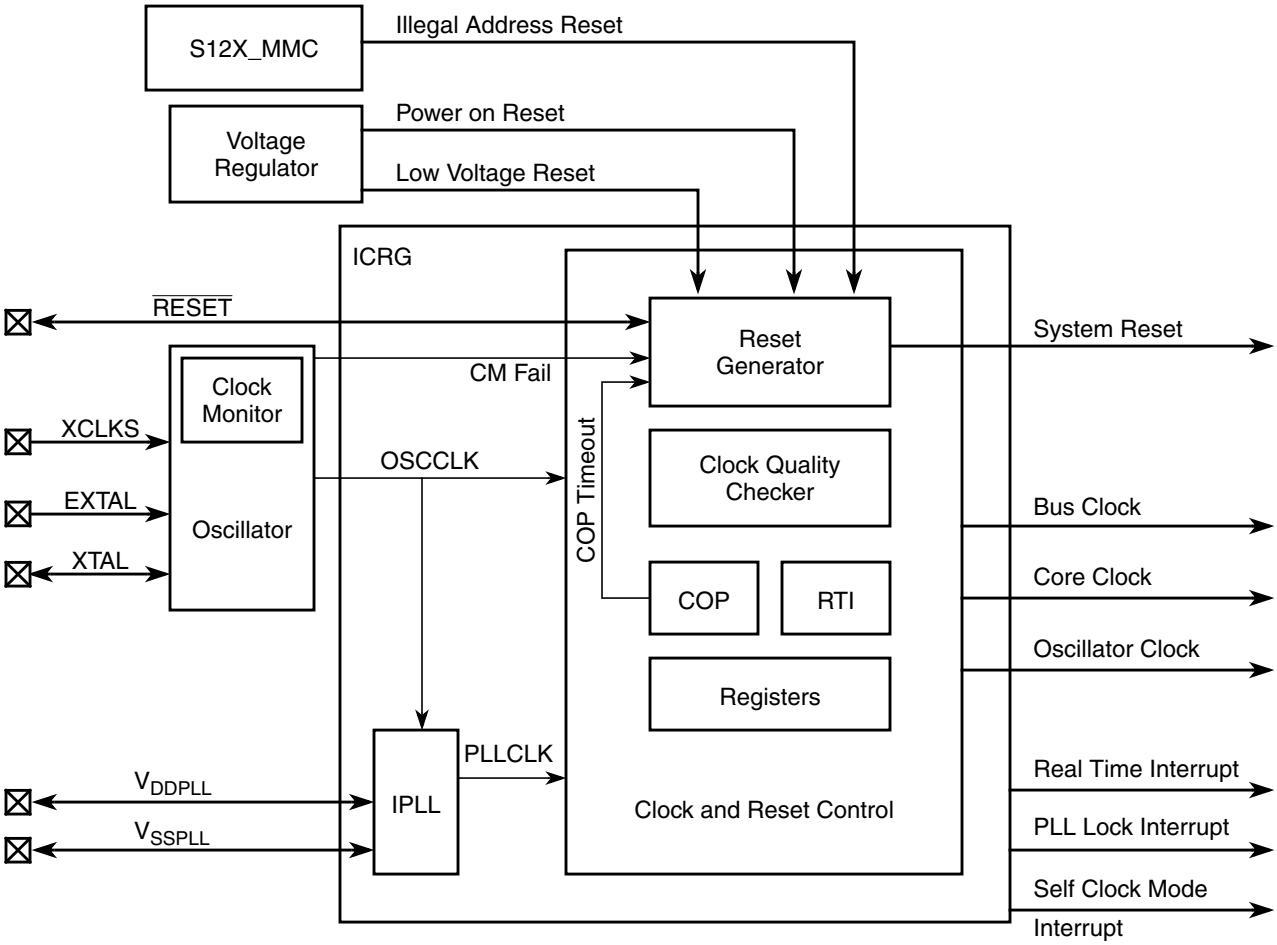


Figure 11-1. Block diagram of S12XECRG

11.2 Signal Description

This section lists and describes the signals that connect off chip.

11.2.1 V_{DDPLL}, V_{SSPLL}

These pins provides operating voltage (V_{DDPLL}) and ground (V_{SSPLL}) for the IPLL circuitry. This allows the supply voltage to the IPLL to be independently bypassed. Even if IPLL usage is not required V_{DDPLL} and V_{SSPLL} must be connected to properly.

11.2.2 $\overline{\text{RESET}}$

$\overline{\text{RESET}}$ is an active low bidirectional reset pin. As an input it initializes the MCU asynchronously to a known start-up state. As an open-drain output it indicates that an system reset (internal to MCU) has been triggered.

11.6.1 Description of Interrupt Operation

11.6.1.1 Real Time Interrupt

The S12XECRG generates a real time interrupt when the selected interrupt time period elapses. RTI interrupts are locally disabled by setting the RTIE bit to zero. The real time interrupt flag (RTIF) is set to1 when a timeout occurs, and is cleared to 0 by writing a 1 to the RTIF bit.

The RTI continues to run during Pseudo Stop Mode if the PRE bit is set to 1. This feature can be used for periodic wakeup from Pseudo Stop if the RTI interrupt is enabled.

11.6.1.2 IPLL Lock Interrupt

The S12XECRG generates a IPLL Lock interrupt when the LOCK condition of the IPLL has changed, either from a locked state to an unlocked state or vice versa. Lock interrupts are locally disabled by setting the LOCKIE bit to zero. The IPLL Lock interrupt flag (LOCKIF) is set to1 when the LOCK condition has changed, and is cleared to 0 by writing a 1 to the LOCKIF bit.

11.6.1.3 Self Clock Mode Interrupt

The S12XECRG generates a Self Clock Mode interrupt when the SCM condition of the system has changed, either entered or exited Self Clock Mode. SCM conditions are caused by a failing clock quality check after power on reset (POR) or low voltage reset (LVR) or recovery from Full Stop Mode (PSTP = 0) or Clock Monitor failure. For details on the clock quality check refer to Section 11.4.1.4, “Clock Quality Checker”. If the clock monitor is enabled (CME = 1) a loss of external clock will also cause a SCM condition (SCME = 1).

SCM interrupts are locally disabled by setting the SCMIE bit to zero. The SCM interrupt flag (SCMIF) is set to1 when the SCM condition has changed, and is cleared to 0 by writing a 1 to the SCMIF bit.

When the third edge occurs, the value previously latched from the serial data input pin is shifted into the LSB or MSB of the SPI shift register, depending on LSBFE bit. After this edge, the next bit of the master data is coupled out of the serial data output pin of the master to the serial input pin on the slave.

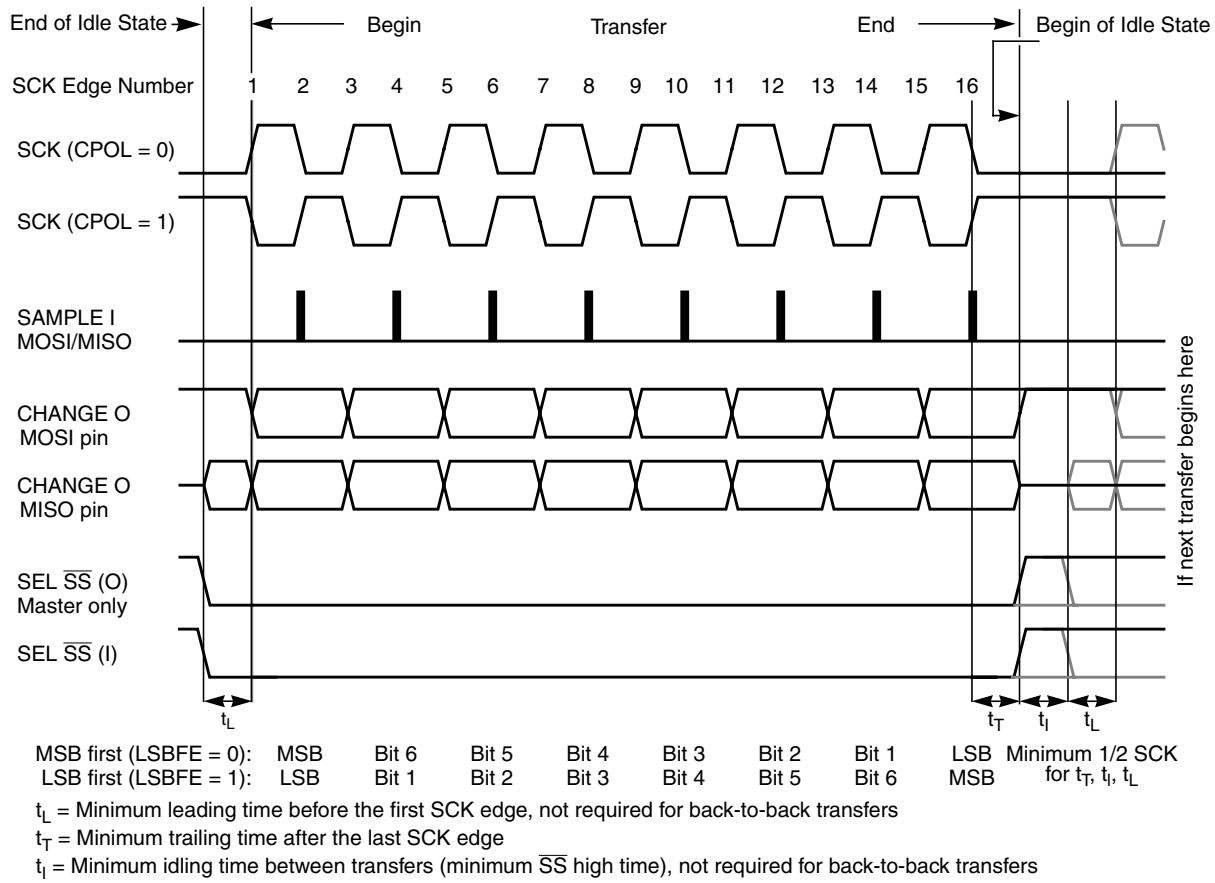
This process continues for a total of n^1 edges on the SCK line with data being latched on even numbered edges and shifting taking place on odd numbered edges.

Data reception is double buffered, data is serially shifted into the SPI shift register during the transfer and is transferred to the parallel SPI data register after the last bit is shifted in.

After $2n^1$ SCK edges:

- Data that was previously in the SPI data register of the master is now in the data register of the slave, and data that was in the data register of the slave is in the master.
- The SPIF flag bit in SPISR is set indicating that the transfer is complete.

Figure 21-14 shows two clocking variations for CPHA = 1. The diagram may be interpreted as a master or slave timing diagram because the SCK, MISO, and MOSI pins are connected directly between the master and the slave. The MISO signal is the output from the slave, and the MOSI signal is the output from the master. The $\overline{SS}$ line is the slave select input to the slave. The $\overline{SS}$ pin of the master must be either high or reconfigured as a general-purpose output not affecting the SPI.



t_L = Minimum leading time before the first SCK edge, not required for back-to-back transfers
t_T = Minimum trailing time after the last SCK edge
t_I = Minimum idling time between transfers (minimum $\overline{SS}$ high time), not required for back-to-back transfers

Figure 21-14. SPI Clock Format 1 (CPHA = 1), with 8-Bit Transfer Width selected (XFRW = 0)

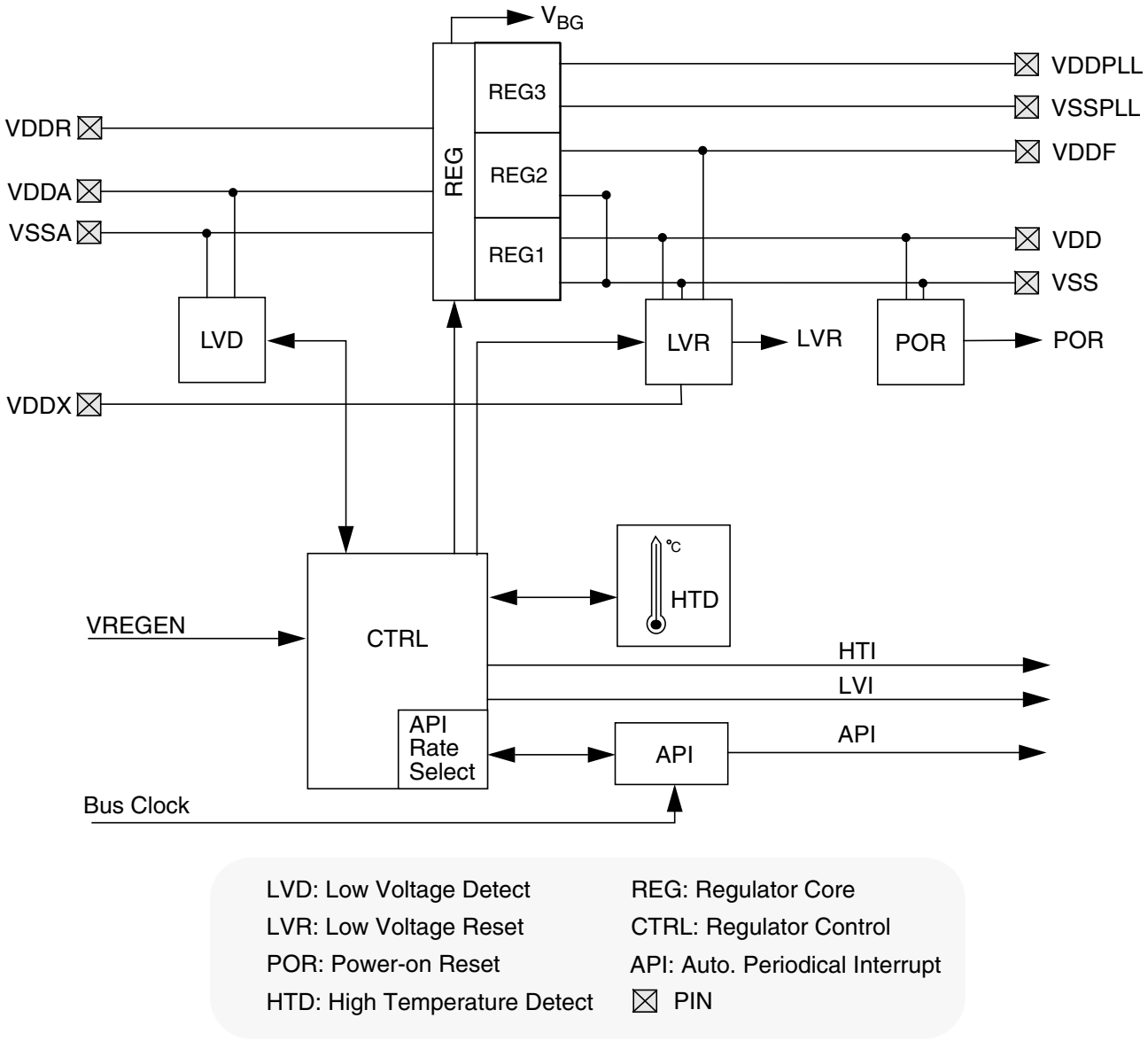


Figure 23-1. VREG_3V3 Block Diagram

2. FDIV shown generates an FCLK frequency of 1.05 MHz

24.3.2.2 Flash Security Register (FSEC)

The FSEC register holds all bits associated with the security of the MCU and Flash module.

Offset Module Base + 0x0001

	7	6	5	4	3	2	1	0
R	KEYEN[1:0]		RNV[5:2]				SEC[1:0]	
W								
Reset	F	F	F	F	F	F	F	F

= Unimplemented or Reserved

Figure 24-6. Flash Security Register (FSEC)

All bits in the FSEC register are readable but not writable.

During the reset sequence, the FSEC register is loaded with the contents of the Flash security byte in the Flash configuration field at global address 0x7F_FF0F located in P-Flash memory (see Table 24-3) as indicated by reset condition F in Figure 24-6. If a double bit fault is detected while reading the P-Flash phrase containing the Flash security byte during the reset sequence, all bits in the FSEC register will be set to leave the Flash module in a secured state with backdoor key access disabled.

Table 24-10. FSEC Field Descriptions

Field	Description
7–6 KEYEN[1:0]	**Backdoor Key Security Enable Bits** — The KEYEN[1:0] bits define the enabling of backdoor key access to the Flash module as shown in Table 24-11.
5–2 RNV[5:2}	**Reserved Nonvolatile Bits** — The RNV bits should remain in the erased state for future enhancements.
1–0 SEC[1:0]	**Flash Security Bits** — The SEC[1:0] bits define the security state of the MCU as shown in Table 24-12. If the Flash module is unsecured using backdoor key access, the SEC bits are forced to 10.

Table 24-11. Flash KEYEN States

KEYEN[1:0]	Status of Backdoor Key Access
00	DISABLED
01	DISABLED(1)
10	ENABLED
11	DISABLED

1. Preferred KEYEN state to disable backdoor key access.

Table 25-15. FCNFG Field Descriptions (continued)

Field	Description
1 FDFD	**Force Double Bit Fault Detect** — The FDFD bit allows the user to simulate a double bit fault during Flash array read operations and check the associated interrupt routine. The FDFD bit is cleared by writing a 0 to FDFD. The FECCR registers will not be updated during the Flash array read operation with FDFD set unless an actual double bit fault is detected. 0 Flash array read operations will set the DFDIF flag in the FERSTAT register only if a double bit fault is detected 1 Any Flash array read operation will force the DFDIF flag in the FERSTAT register to be set (see Section 25.3.2.7) and an interrupt will be generated as long as the DFDIE interrupt enable in the FERCNFG register is set (see Section 25.3.2.6)
0 FSFD	**Force Single Bit Fault Detect** — The FSFD bit allows the user to simulate a single bit fault during Flash array read operations and check the associated interrupt routine. The FSFD bit is cleared by writing a 0 to FSFD. The FECCR registers will not be updated during the Flash array read operation with FSFD set unless an actual single bit fault is detected. 0 Flash array read operations will set the SFDIF flag in the FERSTAT register only if a single bit fault is detected 1 Flash array read operation will force the SFDIF flag in the FERSTAT register to be set (see Section 25.3.2.7) and an interrupt will be generated as long as the SFDIE interrupt enable in the FERCNFG register is set (see Section 25.3.2.6)

25.3.2.6 Flash Error Configuration Register (FERCNFG)

The FERCNFG register enables the Flash error interrupts for the FERSTAT flags.

Offset Module Base + 0x0005

	7	6	5	4	3	2	1	0
R	ERSERIE	PGMERIE	0	EPVIOLIE	ERSVIE1	ERSVIE0	DFDIE	SFDIE
W								
Reset	0	0	0	0	0	0	0	0

= Unimplemented or Reserved

Figure 25-10. Flash Error Configuration Register (FERCNFG)

All assigned bits in the FERCNFG register are readable and writable.

Table 25-16. FERCNFG Field Descriptions

Field	Description
7 ERSERIE	**EEE Erase Error Interrupt Enable** — The ERSERIE bit controls interrupt generation when a failure is detected during an EEE erase operation. 0 ERSERIF interrupt disabled 1 An interrupt will be requested whenever the ERSERIF flag is set (see Section 25.3.2.8)
6 PGMERIE	**EEE Program Error Interrupt Enable** — The PGMERIE bit controls interrupt generation when a failure is detected during an EEE program operation. 0 PGMERIF interrupt disabled 1 An interrupt will be requested whenever the PGMERIF flag is set (see Section 25.3.2.8)
4 EPVIOLIE	**EEE Protection Violation Interrupt Enable** — The EPVIOLIE bit controls interrupt generation when a protection violation is detected during a write to the buffer RAM EEE partition. 0 EPVIOLIF interrupt disabled 1 An interrupt will be requested whenever the EPVIOLIF flag is set (see Section 25.3.2.8)

- 32 Kbytes of D-Flash (Data Flash) memory, consisting of 1 physical Flash block, that can be used as nonvolatile storage to support the built-in hardware scheme for emulated EEPROM, as basic Flash memory primarily intended for nonvolatile data storage, or as a combination of both
- 4 Kbytes of buffer RAM, consisting of 1 physical RAM block, that can be used as emulated EEPROM using a built-in hardware scheme, as basic RAM, or as a combination of both

The Flash memory is ideal for single-supply applications allowing for field reprogramming without requiring external high voltage sources for program or erase operations. The Flash module includes a memory controller that executes commands to modify Flash memory contents or configure module resources for emulated EEPROM operation. The user interface to the memory controller consists of the indexed Flash Common Command Object (FCCOB) register which is written to with the command, global address, data, and any required command parameters. The memory controller must complete the execution of a command before the FCCOB register can be written to with a new command.

CAUTION

A Flash word or phrase must be in the erased state before being programmed. Cumulative programming of bits within a Flash word or phrase is not allowed.

The RAM and Flash memory may be read as bytes, aligned words, or misaligned words. Read access time is one bus cycle for bytes and aligned words, and two bus cycles for misaligned words. For Flash memory, an erased bit reads 1 and a programmed bit reads 0.

It is not possible to read from a Flash block while any command is executing on that specific Flash block. It is possible to read from a Flash block while a command is executing on a different Flash block.

Both P-Flash and D-Flash memories are implemented with Error Correction Codes (ECC) that can resolve single bit faults and detect double bit faults. For P-Flash memory, the ECC implementation requires that programming be done on an aligned 8 byte basis (a Flash phrase). Since P-Flash memory is always read by phrase, only one single bit fault in the phrase containing the byte or word accessed will be corrected.

28.1.1 Glossary

Buffer RAM — The buffer RAM constitutes the volatile memory store required for EEE. Memory space in the buffer RAM not required for EEE can be partitioned to provide volatile memory space for applications.

Command Write Sequence — An MCU instruction sequence to execute built-in algorithms (including program and erase) on the Flash memory.

D-Flash Memory — The D-Flash memory constitutes the nonvolatile memory store required for EEE. Memory space in the D-Flash memory not required for EEE can be partitioned to provide nonvolatile memory space for applications.

Table 28-38. Erase Verify P-Flash Section Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 010 at command launch
		Set if a Load Data Field command sequence is currently active
		Set if command not available in current mode (see Table 28-30)
		Set if an invalid global address [22:0] is supplied(1)
		Set if a misaligned phrase address is supplied (global address [2:0] != 000)
		Set if the requested section crosses a 256 Kbyte boundary
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read(2)
	MGSTAT0	Set if any non-correctable errors have been encountered during the read2
FERSTAT	EPVIOLIF	None

1. As defined by the memory map for FTM1024K5.
2. As found in the memory map for FTM1024K5.

28.4.2.4 Read Once Command

The Read Once command provides read access to a reserved 64 byte field (8 phrases) located in the nonvolatile information register of P-Flash block 0. The Read Once field is programmed using the Program Once command described in Section 28.4.2.7. The Read Once command must not be executed from the Flash block containing the Program Once reserved field to avoid code runaway.

Table 28-39. Read Once Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x04	Not Required
001	Read Once phrase index (0x0000 - 0x0007)	
010	Read Once word 0 value	
011	Read Once word 1 value	
100	Read Once word 2 value	
101	Read Once word 3 value	

Upon clearing CCIF to launch the Read Once command, a Read Once phrase is fetched and stored in the FCCOB indexed register. The CCIF flag will set after the Read Once operation has completed. Valid phrase index values for the Read Once command range from 0x0000 to 0x0007. During execution of the Read Once command, any attempt to read addresses within P-Flash block 0 will return invalid data.

Table 28-59. Set User Margin Level Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 001 at command launch
		Set if a Load Data Field command sequence is currently active
		Set if command not available in current mode (see Table 28-30)
		Set if an invalid global address [22:16] is supplied(1)
		Set if an invalid margin level setting is supplied
	FPVIOL	None
	MGSTAT1	None
	MGSTAT0	None
FERSTAT	EPVIOLIF	None

1. As defined by the memory map for FTM1024K5.

NOTE

User margin levels can be used to check that Flash memory contents have adequate margin for normal level read operations. If unexpected results are encountered when checking Flash memory contents at user margin levels, a potential loss of information has been detected.

28.4.2.14 Set Field Margin Level Command

The Set Field Margin Level command, valid in special modes only, causes the Memory Controller to set the margin level specified for future read operations of a specific P-Flash or D-Flash block.

Table 28-60. Set Field Margin Level Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x0E	Global address [22:16] to identify the Flash block
001	Margin level setting	

Upon clearing CCIF to launch the Set Field Margin Level command, the Memory Controller will set the field margin level for the targeted block and then set the CCIF flag.

Valid margin level settings for the Set Field Margin Level command are defined in Table 28-61.

Table 28-61. Valid Set Field Margin Level Settings

CCOB (CCOBIX=001)	Level Description
0x0000	Return to Normal Level
0x0001	User Margin-1 Level(1)

Table 29-14. FECCRIX Field Descriptions

Field	Description
2-0 ECCRIX[2:0]	**ECC Error Register Index**— The ECCRIX bits are used to select which word of the FECCR register array is being read. See Section 29.3.2.13, “Flash ECC Error Results Register (FECCR),” for more details.

29.3.2.5 Flash Configuration Register (FCNFG)

The FCNFG register enables the Flash command complete interrupt and forces ECC faults on Flash array read access from the CPU or XGATE.

Offset Module Base + 0x0004

	7	6	5	4	3	2	1	0
R	CCIE	0	0	IGNSF	0	0	FDFD	FSFD
W								
Reset	0	0	0	0	0	0	0	0

= Unimplemented or Reserved

Figure 29-9. Flash Configuration Register (FCNFG)

CCIE, IGNSF, FDFD, and FSFD bits are readable and writable while remaining bits read 0 and are not writable.

Table 29-15. FCNFG Field Descriptions

Field	Description
7 CCIE	**Command Complete Interrupt Enable** — The CCIE bit controls interrupt generation when a Flash command has completed. 0 Command complete interrupt disabled 1 An interrupt will be requested whenever the CCIF flag in the FSTAT register is set (see Section 29.3.2.7)
4 IGNSF	**Ignore Single Bit Fault** — The IGNSF controls single bit fault reporting in the FERSTAT register (see Section 29.3.2.8). 0 All single bit faults detected during array reads are reported 1 Single bit faults detected during array reads are not reported and the single bit fault interrupt will not be generated

29.3.2.9.1 P-Flash Protection Restrictions

The general guideline is that P-Flash protection can only be added and not removed. Table 29-23 specifies all valid transitions between P-Flash protection scenarios. Any attempt to write an invalid scenario to the FPROT register will be ignored. The contents of the FPROT register reflect the active protection scenario. See the FPHS and FPLS bit descriptions for additional restrictions.

Table 29-23. P-Flash Protection Scenario Transitions

From Protection Scenario	To Protection Scenario[1]							
	0	1	2	3	4	5	6	7
0	X	X	X	X				
1		X		X				
2			X	X				
3				X				
4				X	X			
5			X	X	X	X		
6		X		X	X		X	
7	X	X	X	X	X	X	X	X

1. Allowed transitions marked with X, see Figure 29-14 for a definition of the scenarios.

29.3.2.10 EEE Protection Register (EPROT)

The EPROT register defines which buffer RAM EEE partition areas are protected against writes.

Offset Module Base + 0x0009

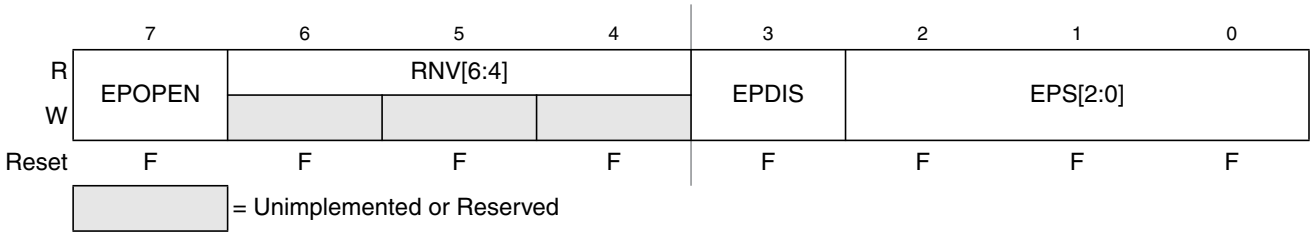


Figure 29-15. EEE Protection Register (EPROT)

All bits in the EPROT register are readable and writable except for RNV[6:4] which are only readable. The EPOPEN and EPDIS bits can only be written to the protected state. The EPS bits can be written anytime until the EPDIS bit is cleared. If the EPOPEN bit is cleared, the state of the EPDIS and EPS bits is irrelevant.

During the reset sequence, the EPROT register is loaded from the EEE protection byte in the Flash configuration field at global address 0x7F_FF0D located in P-Flash memory (see Table 29-3) as indicated by reset condition F in Figure 29-15. To change the EEE protection that will be loaded during the reset sequence, the P-Flash sector containing the EEE protection byte must be unprotected, then the EEE protection byte must be programmed. If a double bit fault is detected while reading the P-Flash phrase

29.4.1.2.1 Define FCCOB Contents

The FCCOB parameter fields must be loaded with all required parameters for the Flash command being executed. Access to the FCCOB parameter fields is controlled via the CCOBIX bits in the FCCOBIX register (see Section 29.3.2.3).

The contents of the FCCOB parameter fields are transferred to the Memory Controller when the user clears the CCIF command completion flag in the FSTAT register (writing 1 clears the CCIF to 0). The CCIF flag will remain clear until the Flash command has completed. Upon completion, the Memory Controller will return CCIF to 1 and the FCCOB register will be used to communicate any results. The flow for a generic command write sequence is shown in Figure 29-26.

CAUTION

A Flash word or phrase must be in the erased state before being programmed. Cumulative programming of bits within a Flash word or phrase is not allowed.

29.4.2.1 Erase Verify All Blocks Command

The Erase Verify All Blocks command will verify that all P-Flash and D-Flash blocks have been erased.

Table 29-33. Erase Verify All Blocks Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x01	Not required

Upon clearing CCIF to launch the Erase Verify All Blocks command, the Memory Controller will verify that the entire Flash memory space is erased. The CCIF flag will set after the Erase Verify All Blocks operation has completed.

Table 29-34. Erase Verify All Blocks Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 000 at command launch
		Set if a Load Data Field command sequence is currently active
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read
	MGSTAT0	Set if any non-correctable errors have been encountered during the read
FERSTAT	EPVIOLIF	None

29.4.2.2 Erase Verify Block Command

The Erase Verify Block command allows the user to verify that an entire P-Flash or D-Flash block has been erased. The FCCOB upper global address bits determine which block must be verified.

Table 29-35. Erase Verify Block Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x02	Global address [22:16] of the Flash block to be verified.

Upon clearing CCIF to launch the Erase Verify Block command, the Memory Controller will verify that the selected P-Flash or D-Flash block is erased. The CCIF flag will set after the Erase Verify Block operation has completed.

maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (e.g., either V_{SS35} or V_{DD35}).

Table A-1. Absolute Maximum Ratings(1)

Num	Rating	Symbol	Min	Max	Unit
1	I/O, regulator and analog supply voltage	V_{DD35}	–0.3	6.0	V
2	Digital logic supply voltage(2)	V_{DD}	–0.3	2.16	V
3	PLL supply voltage2	V_{DDPLL}	–0.3	2.16	V
4	NVM supply voltage2	V_{DDF}	–0.3	3.6	V
5	Voltage difference V_{DDX} to V_{DDA}	Δ_{VDDX}	–6.0	0.3	V
6	Voltage difference V_{SSX} to V_{SSA}	Δ_{VSSX}	–0.3	0.3	V
7	Digital I/O input voltage	V_{IN}	–0.3	6.0	V
8	Analog reference	V_{RH}, V_{RL}	–0.3	6.0	V
9	EXTAL, XTAL	V_{ILV}	–0.3	2.16	V
10	TEST input	V_{TEST}	–0.3	10.0	V
11	Instantaneous maximum current Single pin limit for all digital I/O pins(3)	I_D	–25	+25	mA
12	Instantaneous maximum current Single pin limit for EXTAL, XTAL(4)	I_{DL}	–25	+25	mA
13	Instantaneous maximum current Single pin limit for TEST (5)	I_{DT}	–0.25	0	mA
14	Maximum current Single pin limit for power supply pins	I_{DV}	–100	+100	mA
15	Storage temperature range	T_{stg}	–65	155	°C

1. Beyond absolute maximum ratings device might be damaged.
2. The device contains an internal voltage regulator to generate the logic and PLL supply out of the I/O supply. The absolute maximum ratings apply when the device is powered from an external source.
3. All digital I/O pins are internally clamped to V_{SSX} and V_{DDX}, or V_{SSA} and V_{DDA}.
4. Those pins are internally clamped to V_{SSPLL} and V_{DDPLL}.
5. This pin is clamped low to V_{SSPLL}, but not clamped high. This pin must be tied low in applications.

A.1.6 ESD Protection and Latch-up Immunity

All ESD testing is in conformity with CDF-AEC-Q100 stress test qualification for automotive grade integrated circuits. During the device qualification ESD stresses were performed for the Human Body Model (HBM) and the Charge Device Model.

A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device

specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table A-2. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series resistance	R1	1500	Ohm
	Storage capacitance	C	100	pF
	Number of pulse per pin Positive Negative	 — —	 1 1	
Charged Device	Number of pulse per pin Positive Negative	 — —	 3 3	
Latch-up	Minimum input voltage limit		–2.5	V
	Maximum input voltage limit		7.5	V

Table A-3. ESD and Latch-Up Protection Characteristics

Num	C	Rating	Symbol	Min	Max	Unit
1	C	Human Body Model (HBM)	V_{HBM}	2000	—	V
2	C	Charge Device Model (CDM) corner pins Charge Device Model (CDM) edge pins	V_{CDM}	750 500	— —	V
3	C	Latch-up current at T_A = 125°C Positive Negative	I_{LAT}	 +100 –100	 — —	mA
4	C	Latch-up current at T_A = 27°C Positive Negative	I_{LAT}	 +200 –200	 — —	mA

0x0040–0x007F Enhanced Capture Timer 16-Bit 8-Channels (ECT) Map (Sheet 2 of 3)

Address	Name		Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0x0056	TC3 (hi)	R W	Bit 15	14	13	12	11	10	9	Bit 8
0x0057	TC3 (lo)	R W	Bit 7	6	5	4	3	2	1	Bit 0
0x0058	TC4 (hi)	R W	Bit 15	14	13	12	11	10	9	Bit 8
0x0059	TC4 (lo)	R W	Bit 7	6	5	4	3	2	1	Bit 0
0x005A	TC5 (hi)	R W	Bit 15	14	13	12	11	10	9	Bit 8
0x005B	TC5 (lo)	R W	Bit 7	6	5	4	3	2	1	Bit 0
0x005C	TC6 (hi)	R W	Bit 15	14	13	12	11	10	9	Bit 8
0x005D	TC6 (lo)	R W	Bit 7	6	5	4	3	2	1	Bit 0
0x005E	TC7 (hi)	R W	Bit 15	14	13	12	11	10	9	Bit 8
0x005F	TC7 (lo)	R W	Bit 7	6	5	4	3	2	1	Bit 0
0x0060	PACTL	R W	0	PAEN	PAMOD	PEDGE	CLK1	CLK0	PAOVI	PAI
0x0061	PAFLG	R W	0	0	0	0	0	0	PAOVF	PAIF
0x0062	PACN3 (hi)	R W	PACNT7 (15)	PACNT6 (14)	PACNT5 (13)	PACNT4 (12)	PACNT3 (11)	PACNT2 (10)	PACNT1 (9)	PACNT0 (8)
0x0063	PACN2 (lo)	R W	PACNT7	PACNT6	PACNT5	PACNT4	PACNT3	PACNT2	PACNT1	PACNT0
0x0064	PACN1 (hi)	R W	PACNT7 (15)	PACNT6 (14)	PACNT5 (13)	PACNT4 (12)	PACNT3 (11)	PACNT2 (10)	PACNT1 (9)	PACNT0 (8)
0x0065	PACN0 (lo)	R W	PACNT7	PACNT6	PACNT5	PACNT4	PACNT3	PACNT2	PACNT1	PACNT0
0x0066	MCCTL	R W	MCZI	MODMC	RDMCL	0 ICLAT	0 FLMC	MCEN	MCPR1	MCPR0
0x0067	MCFLG	R W	MCZF	0	0	0	POLF3	POLF2	POLF1	POLF0
0x0068	ICPAR	R W	0	0	0	0	PA3EN	PA2EN	PA1EN	PA0EN
0x0069	DLYCT	R W	DLY7	DLY6	DLY5	DLY4	DLY3	DLY2	DLY1	DLY0
0x006A	ICOVW	R W	NOVW7	NOVW6	NOVW5	NOVW4	NOVW3	NOVW2	NOVW1	NOVW0
0x006B	ICSYS	R W	SH37	SH26	SH15	SH04	TFMOD	PACMX	BUFEN	LATQ
0x006C	OCPD	R W	OCPD7	OCPD6	OCPD5	OCPD4	OCPD3	OCPD2	OCPD1	OCPD0